

Measurements of NitroStrip detectors irradiated with 23MeV protons

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Nitrogen enriched material showed an improvement of some defects after irradiation. NitroStrip is an RD50 project that aims to compare nitrogen enriched silicon wafers with FZ, DOFZ and MCz material. This presentation will show CCE measurements and electrical characterization of NitroStrip samples irradiated at different fluences with 23MeV protons.

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